# N-Channel 60-V (D-S) MOSFET

## **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

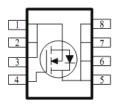
<b>Typical</b>	Ap	plic	atio	ns:
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- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY					
$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$ $I_{D}$					
60	6 @ V <sub>GS</sub> = 10V	19			
00	$6.6 @ V_{GS} = 5.5V$	18			







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter				Limit	Units	
Drain-Source Voltage				60	V	
Gate-Source Voltage				±20	V	
Continuous Drain Correct a		T <sub>A</sub> =25°C		19		
Continuous Drain Current <sup>a</sup>		T <sub>A</sub> =70°C	I <sub>D</sub>	16	Α	
Pulsed Drain Current <sup>b</sup>				75	'	
Continuous Source Current (Diode Conduction) a				5.1	Α	
Dower Dissipation a		T <sub>A</sub> =25°C	P <sub>D</sub>	3.1	W	
Power Dissipation <sup>a</sup>		T <sub>A</sub> =70°C	' D	2.2	V V	
Operating Junction and Storage Temperature Range				-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Ambient	Steady State	IXOJA	80	C/VV		

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

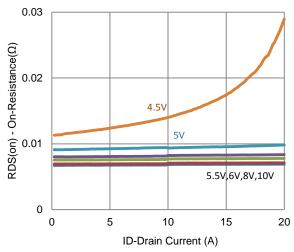
Parameter	Symbol	ol Test Conditions		Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Current	I <sub>DSS</sub>	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}$			6	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 5.5 \text{ V}, I_D = 12 \text{ A}$			6.6	11122	
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 15 \text{ A}$		34		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.73		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = 30 \text{ V}, V_{GS} = 5.5 \text{ V},$		79			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 30 \text{ V}, V_{GS} = 3.3 \text{ V},$ $I_{D} = 15 \text{ A}$		28		nC	
Gate-Drain Charge	$Q_gd$	ID = 13 A		36			
Turn-On Delay Time	t <sub>d(on)</sub>			36			
Rise Time	t <sub>r</sub>	$V_{DS} = 30 \text{ V}, R_L = 2.1 \Omega, I_D = 15 \text{ A},$		74		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN}$ = 10 V, $R_{GEN}$ = 6 $\Omega$		161		ns	
Fall Time	t <sub>f</sub>			49			
Input Capacitance	C <sub>iss</sub>			9818			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		561		pF	
Reverse Transfer Capacitance	$C_{rss}$			501			

#### Notes

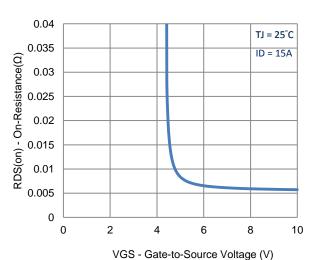
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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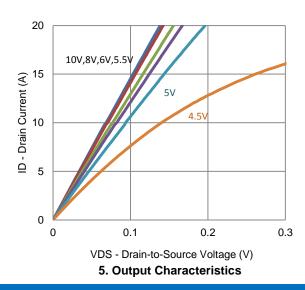
## **Typical Electrical Characteristics**



#### 1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



TJ = 25°C

40

40

40

20

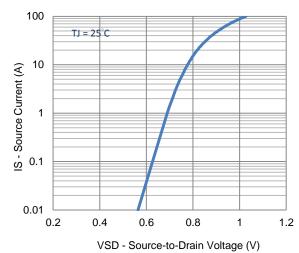
10

0

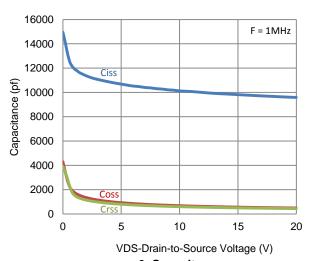
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VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

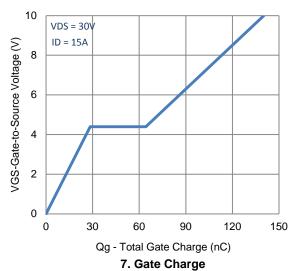


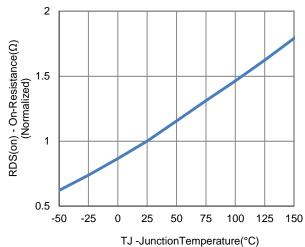
4. Drain-to-Source Forward Voltage

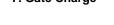


6. Capacitance

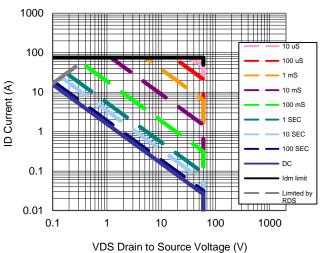
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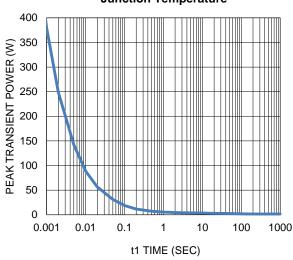






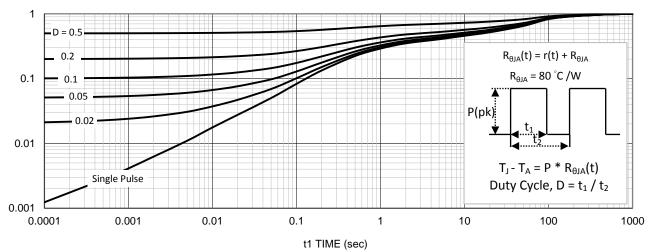






9. Safe Operating Area

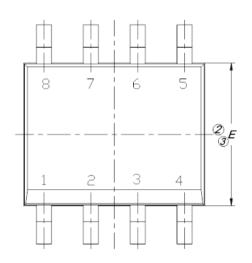
10. Single Pulse Maximum Power Dissipation

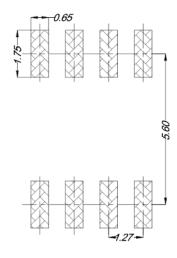


11. Normalized Thermal Transient Junction to Ambient

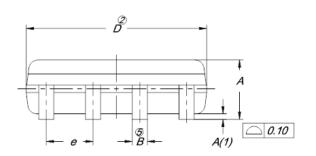
### **Package Information**

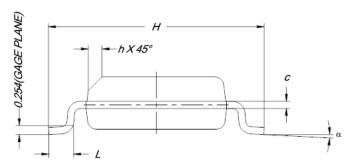
Land Pattern (Only for Reference)





DIM.	MILLIMETERS						
	MIN.	NOM.	MAX.				
Α	1.35	1.55	1.75				
A(1)	0.10	0.18	0.25				
В	0.38	0.45	0.51				
С	0.19	0.22	0.25				
D	4.80	4.90	5.00				
E	3.80	3.90	4.00				
е	1.27 BSC						
Н	5.80	6.00	6.20				
L	0.50	0.72	0.93				
α	0°	4°	8°				
h	0.25	0.38	0.50				





#### Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- 5. Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.